



E <sub>CM</sub> [IeV]	/÷14	14
L <sub>IST</sub> [cm <sup>-2</sup> s <sup>-1</sup> ]	$2 \times 10^{34}$	$5 \div 7.5 \times 10^{34}$
PU	< 50 ÷ 60	140 ÷ 200
L <sub>INT</sub> [fb <sup>-1</sup> ]	300	3000 ÷ 4500

## Resulting in:

- Dose & fluence 10x higher
- 750 kHz L1 rate
- 12.5 µs L1 latency

The present CMS tracker cannot sustain the foreseen radiation levels and data rates and has to be

completely replaced



• Operation at -20°C

> 1.2 Grad, TID

Innovative power scheme





## CMS Read Out Chip (CROC)

- CMS chip size (16.8×21.6 mm<sup>2</sup>, 336×432 cells)
- 65 nm CMOS technology
- Dead time ≤1% @3.2 GHz/cm<sup>2</sup>
- 1 Grad TID resistant
- Strongly protected against SEU effects
- $50 \times 50 \ \mu m^2 \ cell$
- Linear analog FE

• Shunt-LDO:

> On chip solution

- low threshold ( $\leq 1000 \text{ e}$ -)
- High hit and trigger rate
- (up to 4×1.28 Gb/s output links)
- Serial powering capabilities



## Services

- Portcards: •
  - > 3 LpGBT
  - > 3 VTRX+
  - > 1 bPOL12V DC/DC converter
  - > 1 bPOL2V5 DC/DC converter







## 432 pixels (21.6 mm)



Serial powering • Consecutive modules use the same current • Current is shared in parallel between: > ROCs in the same module (2 or 4) 1.5 V



- Powering:
  - > Low voltage power with serial powering scheme over 576 chains
  - > High voltage distributed in parallel to modules in each serial chain
  - > ~ 350 pre-heaters meeded by cooling



> Low mass, radiation hard, no extra ASIC

> ROC IP block for serial powering support

> Analog and Digital domain on ROC

- > Shunt functionality needed to implement the serial scheme
- > LDO regulation needed to ensure the correct voltage to the electronics ( $\sim 1.2$  V)
- > Equivalent to a resistor in series with
- a voltage source  $(R_{eff}, V_{offset})$

- $25 \times 100 \ \mu m^2$  pixel cells •
- $50 \times 50 \ \mu m^2$  bump bond pads ٠
- Extensive R&D program •
- Irradiations and test beams (CERN, Fermilab, Desy, FNAL)
- Simulations for geometry optimization
- Thin planar n-in-p sensors:
  - > 150  $\mu$ m thickness
  - > Bitten implant, no punch-through bias dot
  - > Hit efficiency > 99% (after  $2 \times 10^{16} n_{eq}/cm^2$ )
- 3D pixel sensors on Barrel layer1:
  - > Lower high voltage power consuption
  - > Stable hit resolution up to  $10^{16} n_{eq}/cm^2$

